



SINGLE 2 INPUT POSITIVE NAND GATE

Description

The 74LVC1G00 is a single 2-input positive NAND gate with a standard push-pull output. The device is designed for operation with a power supply range of 1.65V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output preventing damaging current backflow when the device is powered down.

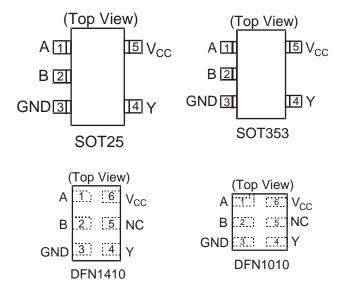
The gate performs the positive Boolean function:

$$Y = \overline{A \bullet B}$$
 or $Y = \overline{A} + \overline{B}$

Features

- Wide Supply Voltage Range from 1.65 to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Tested per JESD 22
 - Exceeds 200-V Machine Model (A115-A)
 - o Exceeds 2000-V Human Body Model (A114-A)
 - Exceeds 1000-V Charged Device Model (C101C)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- Direct Interface with TTL Levels
- All packages Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)

Pin Assignments



Applications

- Voltage Level Shifting
- General Purpose Logic
- Power Down Signal Isolation
- Wide array of products such as.
 - o PCs, networking, notebooks, netbooks, PDAs
 - o Tablet Computers, E-readers
 - o Computer peripherals, hard drives, CD/DVD ROM
 - o TV, DVD, DVR, set top box
 - o Cell Phones, Personal Navigation / GPS
 - o MP3 players ,Cameras, Video Recorders

Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead_free.html



Y

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b-

Logic Diagram

A B

2

Pin Descriptions

Pin Name	Description	
А	Data Input	
В	Data Input	
GND	Ground	
Y	Data Output	
V _{CC}	Supply Voltage	
NC	No Connection	

Function Table

Inp	Output	
А	В	Y
Н	Н	L
L	Х	Н
Х	L	Н

Absolute Maximum Ratings (Note 2)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD CDM	Charged Device Model ESD Protection	1	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or I _{OFF} state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current VI<0	-50	mA
Ι _{ΟΚ}	Output Clamp Current	-50	mA
Ι _Ο	Continuous output current	±50	mA
I _{CC,} I _{GND}	Continuous current through V _{CC} or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Notes: 2. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

NEW PRODUCT



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Recommended Operating Conditions (Note 3)

Symbol		Parameter	Min	Max	Unit	
V		Operating	1.65	5.5	V	
V _{CC}	Operating Voltage	Data retention only	1.5		V	
		V _{CC} = 1.65V to 1.95V	0.65 X V _{CC}			
M	Llink laval lanut Valtana	$V_{CC} = 2.3V \text{ to } 2.7V$	1.7		V	
VIH	High-level Input Voltage	V _{CC} = 3V to 3.6V	2		V	
		$V_{CC} = 4.5V$ to 5.5V	0.7 X V _{CC}			
		V _{CC} = 1.65V to 1.95V		0.35 X V _{CC}		
	Level and Second configure	$V_{CC} = 2.3V \text{ to } 2.7V$		0.7		
VIL	Low-level input voltage	V _{CC} = 3V to 3.6V		0.8	V	
		$V_{CC} = 4.5V \text{ to } 5.5V$		0.3 X V _{CC}		
VI	I	nput Voltage	0	5.5	V	
Vo	C	output Voltage	0	V _{CC}	V	
	High-level output current	V _{CC} = 1.65V		-4		
		$V_{CC} = 2.3V$		-8		
I _{OH}		High-level output current			-16	mA
			$V_{CC} = 3V$		-24	
		$V_{CC} = 4.5V$		-32		
		V _{CC} = 1.65V		4		
		$V_{CC} = 2.3V$		8		
I _{OL}	Low-level output current	<u>)/ 2)/</u>		16	mA	
		$V_{CC} = 3V$		24		
		$V_{CC} = 4.5V$		32		
		$V_{CC} = 1.8V \pm 0.15V, 2.5V \pm 0.2V$		20		
Δt/ΔV	Input transition rise or fall	$V_{CC} = 3.3V \pm 0.3V$		10	ns/V	
	rate	$V_{CC} = 5V \pm 0.5V$		5		
T _A	Operating free-air temperature		-40	125	°C	

Notes: 3. Unused inputs should be held at $V_{\mbox{CC}}$ or Ground.



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Electrical Characteristics (All typical values are at V_{CC} = 3.3V, T_A = 25°C)

Symbol Parameter		Takon In	N	-40	°C to 85	Эv	-40°C to	125ºC	Unit
Symbol	Parameter	Test Conditions	Vcc	Min	Тур.	Max	Min	Max	Unit
		I _{OH} = -100μA	1.65V to 5.5V	$V_{CC} - 0.1$			$V_{CC} - 0.1$		
		I _{OH} = -4mA	1.65V	1.2			0.95		
V	High Level	I _{OH} = -8mA	2.3V	1.9			1.7		V
V _{OH}	Output Voltage	I _{OH} = -16mA	3V	2.4			2.2		v
	Vollago	I _{OH} = -24mA	3V	2.3			2.0		
		I _{OH} = -32mA	4.5V	3.8			3.4		
		I _{OL} = 100μA	1.65V to 5.5V			0.1		0.1	
		I _{OL} = 4mA	1.65V			0.45		0.7	
_	Low Level	I _{OL} = 8mA	2.3V			0.3		0.45	V
V _{OL}	Output Voltage	I _{OL} = 16mA	3V			0.4		0.6	v
	Vollago	I _{OL} = 24mA				0.55		0.8	
		$I_{OL} = 32 \text{mA}$	4.5V			0.55		.8	
l _l	Input Current	$V_{I} = 5.5V \text{ or GND}$	0 to 5.5V		± 0.1	±5		± 100	μA
I _{OFF}	Power Down Leakage Current	$V_{I} \text{ or } V_{O} = 5.5 V$	0V			±10		±200	μA
I _{CC}	Supply Current	V _I = 5.5V or GND I _O =0	5.5V		0.1	10		200	μA
ΔI _{CC}	Additional Supply Current	One input at V_{CC} – 0.6V Other inputs at V _{CC} or GND	3V to 5.5V			500		5000	μA
Ci	Input Capacitance	$V_i = V_{CC} - or GND$	3.3V		5				pF

Package Characteristics (All typical values are at $V_{CC} = 3.3V$, $T_A = 25^{\circ}C$)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Unit
		SOT25			204		
0	Thermal Resistance	SOT353	(Note 4)		371		°C/W
θ_{JA}	Junction-to-Ambient	DFN1010	(Note 4)		445		
		DFN1410			460		
		SOT25	(Note 4)		52		
0	Thermal Resistance	SOT35			143		°C/W
θ _{JC}	Junction-to-Case	DFN1010			250		
		DFN1410			265		

Notes: 4. Test condition for SOT25, SOT353, DFN1410 and DFN1010: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



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Switching Characteristics

Figure 1	Typical Values at T ₄ -	- 25 °C and nominal voltages	s 1.8V, 2.5V, 2.7V, 3.3V, and 5.0V.
i iyure i	i ypical values at T _A -	- 25 C and nonninal vollages	51.00, 2.00, 2.70, 5.00, and 5.00.

Baramatar From		Parameter	То	V	T _A	= -40°C to 8	5°C	T _A = -40°C	C to 125⁰C	Unit
Parameter	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Unit	
		1.8V ± 0.15V	1.0	3.3	8.0	1.0	10.5			
			2.5V ± 0.2V	0.5	2.2	5.5	0.5	7.0		
t _{pd}	A or B	Y	2.7V	0.5	2.6	5.8	0.5	7.5	ns	
			3.3V ± 0.3V	0.5	2.2	4.7	0.5	6.0		
			5.0V ± 0.5V	0.5	1.8	4.0	0.5	5.5		

Operating Characteristics

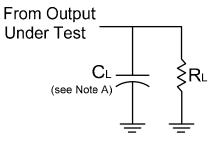
T_A = 25 °C

Parameter		Test Conditions	V _{CC} = 1.8V Typ.	V _{CC} = 2.5V Typ.	V _{CC} = 3.3V Typ.	V _{CC} = 5V Typ.	Unit
C _{pd}	Power dissipation capacitance	f = 10 MHz	22	22	23	25	pF

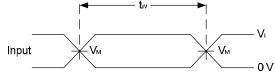


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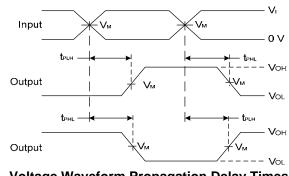
Parameter Measurement Information



V _{cc}	Inputs		V _M	CL	RL
vcc	VI	t _r /t _f	¥ M	UL CL	κ <u>ι</u>
1.8V ± 0.15V	V _{CC}	≤2ns	V _{CC} /2	30 pF	1 KΩ
2.5V ± 0.2V	V _{CC}	≤2ns	V _{CC} /2	30 pF	500 Ω
2.7V	V _{CC}	≤2.5ns	1.5V	50 pF	500 Ω
3.3V ± 0.3V	3.0V	≤2.5ns	1.5V	50 pF	500 Ω
$5.0V \pm 0.5V$	V _{CC}	≤2.5ns	V _{CC} /2	50 pF	500 Ω



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1. Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

B. All pulses are supplied at pulse repetition rate \leq 10 MHz.

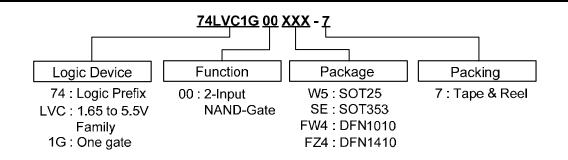
C. Inputs are measured separately one transition per measurement.

D. t_{PLH} and t_{PHL} are the same as $t_{PD.}$



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Ordering Information



Ζ

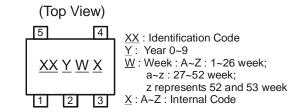
	Device	Package	Packaging	7" Tape a	Ind Reel
	Device	Code	(Note 6)	Quantity	Part Number Suffix
Pb ,	74LVC1G00W5-7	W5	SOT25	3000/Tape & Reel	-7
•	74LVC1G00SE-7	SE	SOT353	3000/Tape & Reel	-7
Pb,	74LVC1G00FW4-7	FW4	DFN1010	5000/Tape & Reel	-7
B	74LVC1G00FZ4-7	FZ4	DFN1410	5000/Tape & Reel	-7

5. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf. Notes:

6. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf

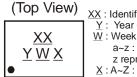
Marking Information

(1) SOT25 and SOT353



Part Number	Package	Identification Code
74LVC1G00W5	SOT25	US
74LVC1G00SE	SOT353	US

(2) DFN1010 and DFN1410



XX : Identification Code Year 0~9 \underline{W} : Week : A~Z : 1~26 week; a~z: 27~52 week; z represents 52 and 53 week X : A~Z : Internal Code

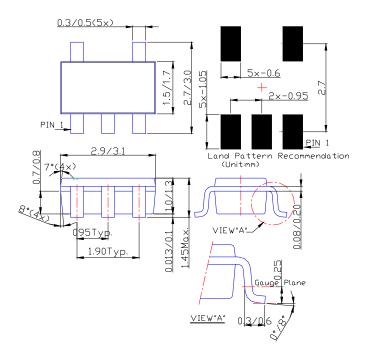
Part Number	Package	Identification Code
74LVC1G00FW4	DFN1010	US
74LVC1G00FZ4	DFN1410	US



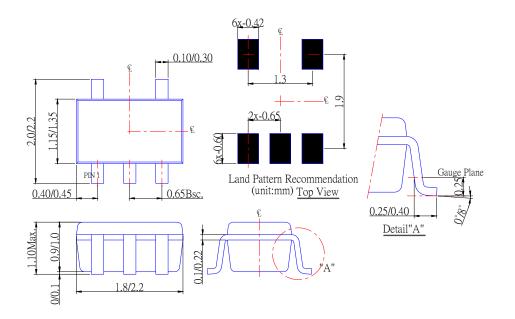
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Package Outline Dimensions (All Dimensions in mm)

(1) Package Type: SOT25



(2) Package Type: SOT353

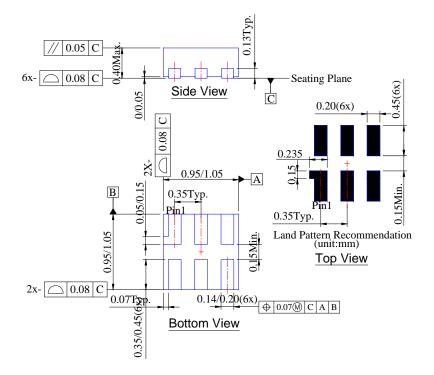




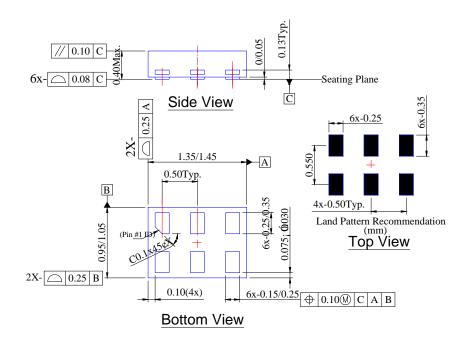
SINGLE 2 INPUT POSITIVE NAND GATE

Package Outline Dimensions (cont.)

(3) Package Type DFN1010



(4) Package Type DFN1410





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